

IGBT & Diode Modules Type Designation

IGBT & Diode: BSM modules

BSM	100	GB	120	D	N2	K	
B							Silicon
							Type:
S							S=Switch
Y							Y= Diode
M							Mechanical construction: Module
	100						Max. DC-collector current in A
		G					Technology: G= IGBT-technology
							Configuration:
		A					Single switch/ diode
		P					PIM: Power Integrated Module
		B					Halfbridge
		D					3 phase full bridge
		T					Tripack
		AL					Chopper: Diode connected to Collector
		AR					Chopper: Diode connected to Emitter
			120				Max. Collector-emitter-voltage in 10 V
				D			With fast internal diode
					N		Low inductance module design
					L		Low Loss IGBT Chip
						2	2 nd generation silicon
						C	With EmCon-Diode
						K	Construction variation
						G	Construction variation
						S	Collector sense
						E	special type with code no. xxxx

IGBT& Modules Type Designation IGBT

IGBT & Diode: IHM / IHV & all new eupec modules

FF	800	R	17	K	F	6	D	B2	
FF									Dual Switch
FZ									Single Switch
FS									3 phase full bridge
FP									Power Integrated Modul
F4-									One phase bridge
FD									Chopper config.
DD									Dual Diode
									(for circuit see outline)
	800								Max. DC-collector current in A
		R							Type:
		S							Reverse conducting
			17						Fast diode
				K					Collector-emitter-voltage in 100 V
					F				Mechanical construction: Module
					L				Fast switching IGBT Chip
					S				Low Loss IGBT Chip
					E				fast Short tail IGBT Chip
						1..n			Low Sat & fast IGBT Chip
						C			Internal reference numbers
						D			With EmCon diode
						G			Higher diode current
							B1..n		Module in Big housing
							S1..n		Construction Variation
									Electrical selection

Definition of Saturation Voltage